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PATENT

Customer No. 22,852

Attorney Docket No. 07553.0020-00000

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
Takeshi SAITO et al.) Group Art Unit: 1765
Application No.: 09/807,896) Examiner: S. Ahmed
Filed: April 19, 2001)
For: PLASMA ETCHING METHOD)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

AMENDMENT

In reply to the Office Action dated April 2, 2003, please amend the application as follows:

IN THE CLAIMS:

Please cancel claims 7-11 without prejudice or disclaimer, amend claim 1, and add new claim 12, as follows:

1. (Amended) A plasma etching method for implementing a specific etching process on a workpiece placed on an electrode provided within a processing chamber by introducing a processing gas into said processing chamber, generating plasma inside said processing chamber with a plasma source and applying biasing power to said electrode, wherein;

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